

AMENDMENTS

IN THE CLAIMS

Please amend the claims as follows.

[15] 17. The method of claim 1 wherein said top level metal for interconnecting lines and top level metal for bond pads are formed within or on top of any layer of a semiconductor device other than or in addition to said semiconductor substrate.

[16] 18. The method of claim 1 wherein said top level metal for interconnecting lines and top level metal for bond pads are formed selectively on the bare main surface of a semiconductor

REMARKS

Examiner N. Berezny is thanked for his thorough examination of the Prior Art.

Favorable reconsideration of this application in light of the above amendments and the following remarks is respectfully requested.